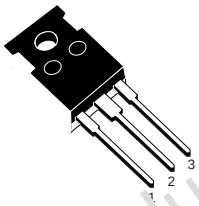
# STW20NK70Z

## N-CHANNEL 700V - 0.25Ω - 20A TO-247
## Zener-Protected SuperMESH™ MOSFET

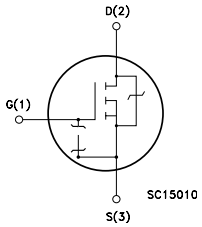
| TYPE | $V_{DSS}$ | $R_{DS(on)}$ | $I_D$ | Pw |
|---|---|---|---|---|
| STW20NK70Z | 700 V | < 0.285 Ω | 20 A | 350 W |

- TYPICAL $R_{DS}(on)$ = 0.25 Ω
- EXTREMELY HIGH dv/dt CAPABILITY
- 100% AVALANCHE TESTED
- GATE CHARGE MINIMIZED
- VERY LOW INTRINSIC CAPACITANCES
- VERY GOOD MANUFACTURING REPEATIBILITY




TO-247

**INTERNAL SCHEMATIC DIAGRAM**




### DESCRIPTION

The SuperMESH™ series is obtained through an extreme optimization of ST's well established strip-based PowerMESH™ layout. In addition to pushing on-resistance significantly down, special care is taken to ensure a very good dv/dt capability for the most demanding applications. Such series complements ST full range of high voltage MOSFETs including revolutionary MDmesh™ products.

### APPLICATIONS

- HIGH CURRENT, HIGH SPEED SWITCHING
- IDEAL FOR OFF-LINE POWER SUPPLIES

Obsolete Product(s) - Obsolete Product(s)
Obsolete Product(s) - Obsolete Product(s)

### ORDER CODES

| PART NUMBER | MARKING | PACKAGE | PACKAGING |
|---|---|---|---|
| STW20NK70Z | W20NK70Z | TO-247 | TUBE |

## ABSOLUTE MAXIMUM RATINGS

| Symbol | Parameter | Value | Unit |
|---|---|---|---|
| $V_{DS}$ | Drain-source Voltage ($V_{GS}$ = 0) | 700 | V |
| $V_{DGR}$ | Drain-gate Voltage ($R_{GS}$ = 20 kΩ) | 700 | V |
| $V_{GS}$ | Gate- source Voltage | ± 30 | V |
| $I_D$ | Drain Current (continuous) at $T_C$ = 25°C | 20 | A |
| $I_D$ | Drain Current (continuous) at $T_C$ = 100°C | 12 | A |
| $I_{DM}$ (•) | Drain Current (pulsed) | 80 | A |
| $P_{TOT}$ | Total Dissipation at $T_C$ = 25°C | 350 | W |
| | Derating Factor | 2.77 | W/°C |
| $V_{ESD(G-S)}$ | Gate source ESD(HBM-C=100pF, R=1.5KΩ) | 6000 | V |
| dv/dt (1) | Peak Diode Recovery voltage slope | 4.5 | V/ns |
| $T_j$<br>$T_{stg}$ | Operating Junction Temperature<br>Storage Temperature | -55 to 150 | °C |

(•) Pulse width limited by safe operating area
(1) $I_{SD} \leq 20A$, $di/dt \leq 200$ A/µs, $V_{DD} \leq V_{(BR)DSS}$, $T_j \leq T_{JMAX.}$
(*) Limited only by maximum temperature allowed

## THERMAL DATA

| | | | |
|---|---|---|---|
| Rthj-case | Thermal Resistance Junction-case Max | 0.36 | °C/W |
| Rthj-amb<br>$T_l$ | Thermal Resistance Junction-ambient Max<br>Maximum Lead Temperature For Soldering Purpose | 50<br>300 | °C/W<br>°C |

## AVALANCHE CHARACTERISTICS

| Symbol | Parameter | Max Value | Unit |
|---|---|---|---|
| $I_{AR}$ | Avalanche Current, Repetitive or Not-Repetitive (pulse width limited by $T_j$ max) | 19 | A |
| $E_{AS}$ | Single Pulse Avalanche Energy (starting $T_j$ = 25 °C, $I_D = I_{AR}$, $V_{DD}$ = 50 V) | 300 | mJ |

## GATE-SOURCE ZENER DIODE

| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Unit |
|---|---|---|---|---|---|---|
| $BV_{GSO}$ | Gate-Source Breakdown Voltage | Igs=± 1mA (Open Drain) | 30 | | | V |

## PROTECTION FEATURES OF GATE-TO-SOURCE ZENER DIODES

The built-in back-to-back Zener diodes have specifically been designed to enhance not only the device's ESD capability, but also to make them safely absorb possible voltage transients that may occasionally be applied from gate to source. In this respect the Zener voltage is appropriate to achieve an efficient and cost-effective intervention to protect the device's integrity. These integrated Zener diodes thus avoid the usage of external components.

Obsolete Product(s) - Obsolete Product(s)
Obsolete Product(s) - Obsolete Product(s)

**ELECTRICAL CHARACTERISTICS** ($T_{CASE}$ =25°C UNLESS OTHERWISE SPECIFIED)

ON/OFF

| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Unit |
|---|---|---|---|---|---|---|
| $V_{(BR)DSS}$ | Drain-source Breakdown Voltage | $I_D$ = 1 mA, $V_{GS}$ = 0 | 700 | | | V |
| $I_{DSS}$ | Zero Gate Voltage Drain Current ($V_{GS}$ = 0) | $V_{DS}$ = Max Rating<br>$V_{DS}$ = Max Rating, $T_C$ = 125 °C | | | 1<br>50 | µA<br>µA |
| $I_{GSS}$ | Gate-body Leakage Current ($V_{DS}$ = 0) | $V_{GS}$ = ± 20V | | | ±10 | µA |
| $V_{GS(th)}$ | Gate Threshold Voltage | $V_{DS}$ = $V_{GS}$, $I_D$ = 150 µA | 3 | 3.75 | 4.5 | V |
| $R_{DS(on)}$ | Static Drain-source On Resistance | $V_{GS}$ = 10V, $I_D$ = 10 A | | 0.25 | 0.285 | Ω |

DYNAMIC

| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Unit |
|---|---|---|---|---|---|---|
| $g_{fs}$ (1) | Forward Transconductance | $V_{DS}$ = 15 V, $I_D$ = 10 A | | 18 | | S |
| $C_{iss}$<br>$C_{oss}$<br>$C_{rss}$ | Input Capacitance<br>Output Capacitance<br>Reverse Transfer Capacitance | $V_{DS}$ = 25V, f = 1 MHz, $V_{GS}$ = 0 | | 6000<br>550<br>118 | | pF<br>pF<br>pF |
| $C_{oss\ eq.}$ (3) | Equivalent Output Capacitance | $V_{GS}$ = 0V, $V_{DS}$ = 0V to 640V | | 310 | | pF |
| $t_{d(on)}$<br>$t_r$<br>$t_{d(off)}$<br>$t_f$ | Turn-on Delay Time<br>Rise Time<br>Turn-off Delay Time<br>Fall Time | $V_{DD}$ = 350 V, $I_D$ = 10A<br>$R_G$ = 4.7Ω $V_{GS}$ = 10 V<br>(Resistive Load see, Figure 3) | | 42<br>33<br>130<br>38 | | ns<br>ns<br>ns<br>ns |
| $Q_g$<br>$Q_{gs}$<br>$Q_{gd}$ | Total Gate Charge<br>Gate-Source Charge<br>Gate-Drain Charge | $V_{DD}$ = 560V, $I_D$ = 20 A,<br>$V_{GS}$ = 10V | | 185<br>38<br>92 | | nC<br>nC<br>nC |

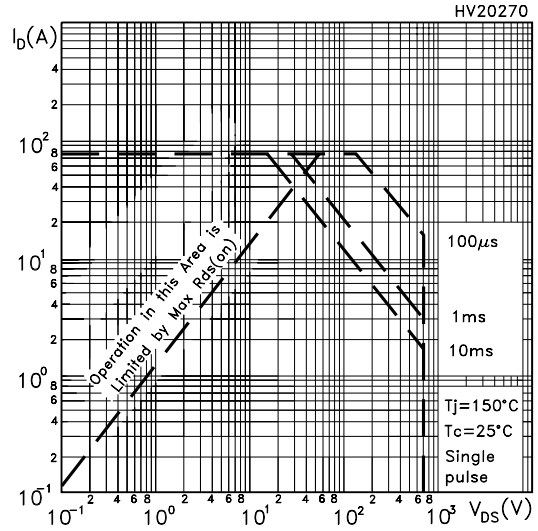
SOURCE DRAIN DIODE

| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Unit |
|---|---|---|---|---|---|---|
| $I_{SD}$<br>$I_{SDM}$ (2) | Source-drain Current<br>Source-drain Current (pulsed) | | | | 20<br>80 | A<br>A |
| $V_{SD}$ (1) | Forward On Voltage | $I_{SD}$ = 20 A, $V_{GS}$ = 0 | | | 1.6 | V |
| $t_{rr}$<br>$Q_{rr}$<br>$I_{RRM}$ | Reverse Recovery Time<br>Reverse Recovery Charge<br>Reverse Recovery Current | $I_{SD}$ = 20 A, di/dt = 100 A/µs<br>$V_{DD}$ = 100 V, $T_j$ = 25°C<br>(see test circuit, Figure 5) | | 940<br>16<br>35 | | ns<br>µC<br>A |
| $t_{rr}$<br>$Q_{rr}$<br>$I_{RRM}$ | Reverse Recovery Time<br>Reverse Recovery Charge<br>Reverse Recovery Current | $I_{SD}$ = 20 A, di/dt = 100A/µs<br>$V_{DD}$ = 100 V, $T_j$ = 150°C<br>(see test circuit, Figure 5) | | 772<br>13<br>33 | | ns<br>µC<br>A |

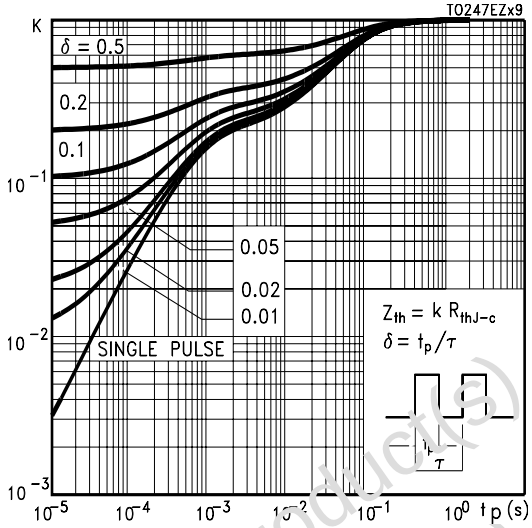
Note: 1. Pulsed: Pulse duration = 300 µs, duty cycle 1.5 %.
2. Pulse width limited by safe operating area.
3. $C_{oss\ eq.}$ is defined as a constant equivalent capacitance giving the same charging time as $C_{oss}$ when $V_{DS}$ increases from 0 to 80% $V_{DSS}$.

Obsolete Product(s) - Obsolete Product(s)

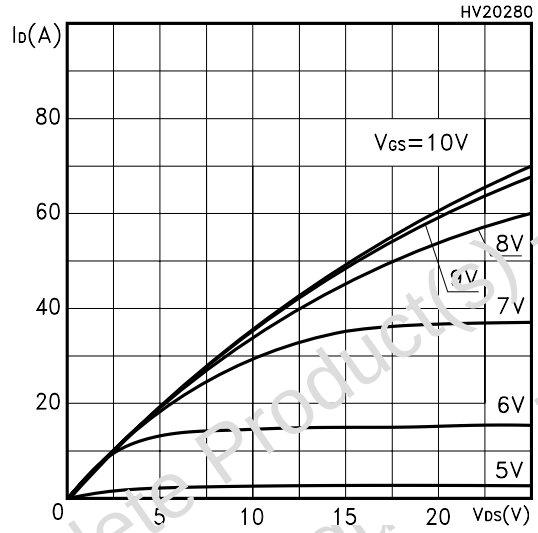
### Safe Operating Area



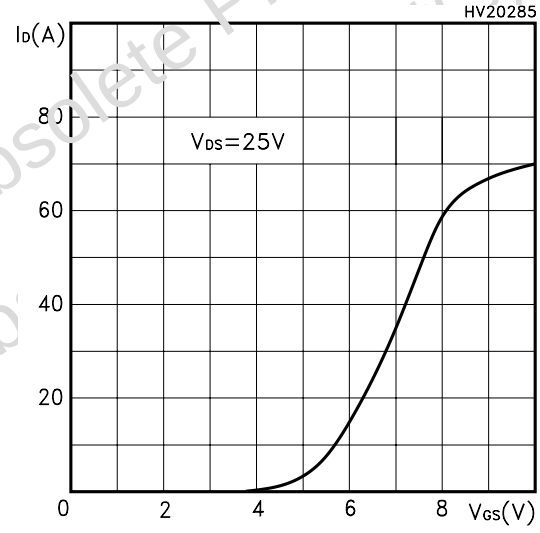

### Thermal Impedance



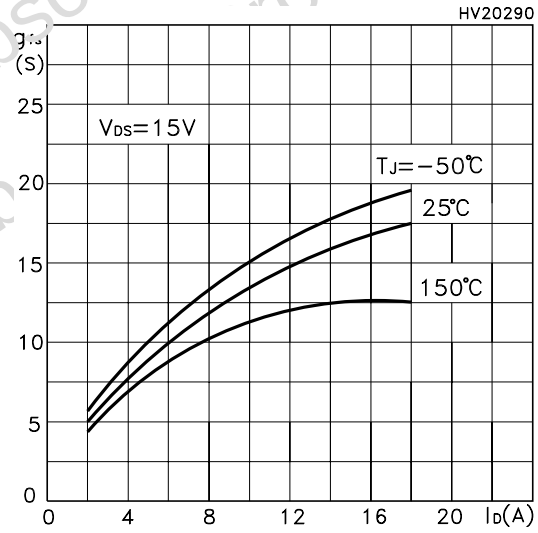

### Output Characteristics



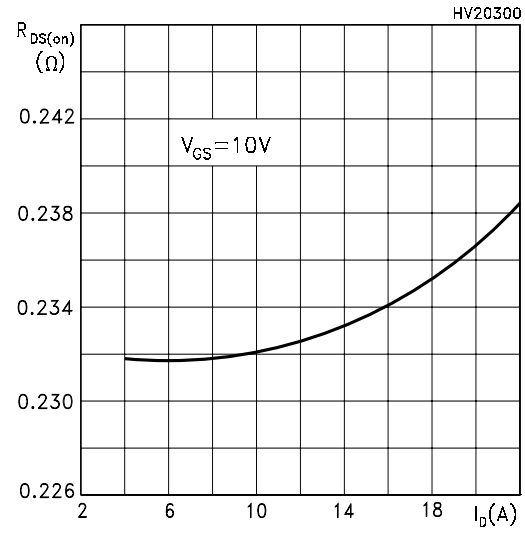

### Transfer Characteristics




### Transconductance

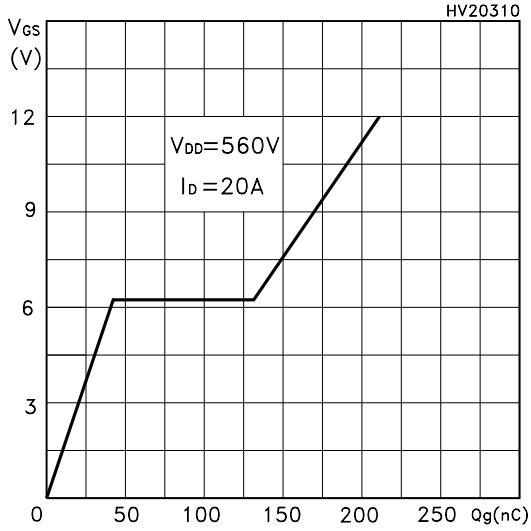



### Static Drain-source On Resistance

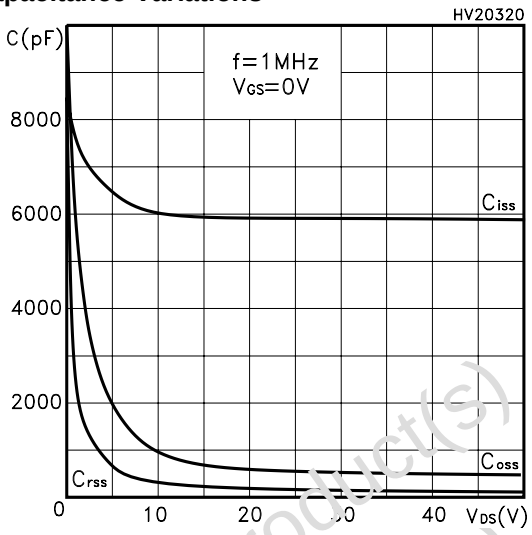



Obsolete Product(s) - Obsolete Products(s)

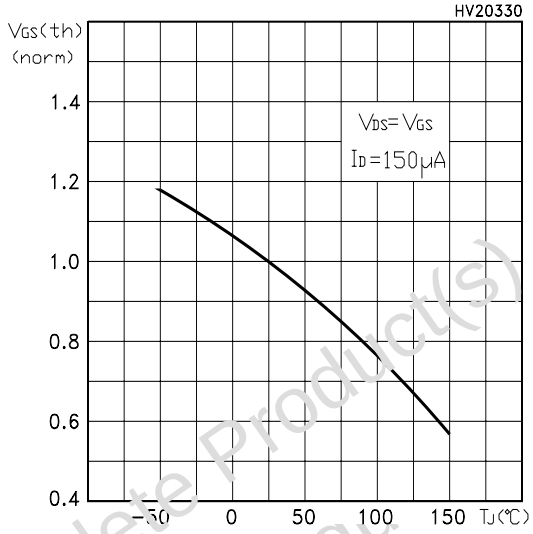
### Gate Charge vs Gate-source Voltage



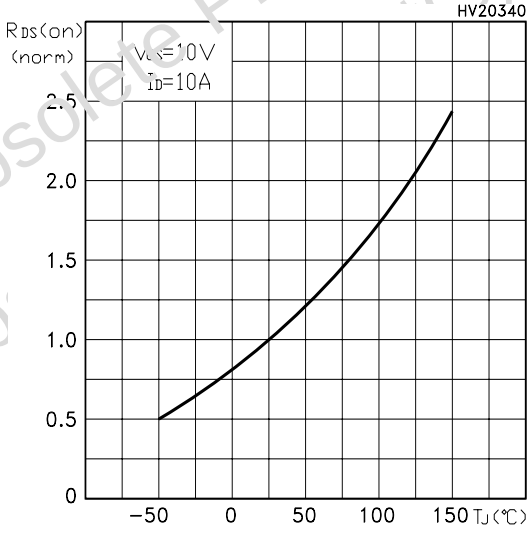

### Capacitance Variations



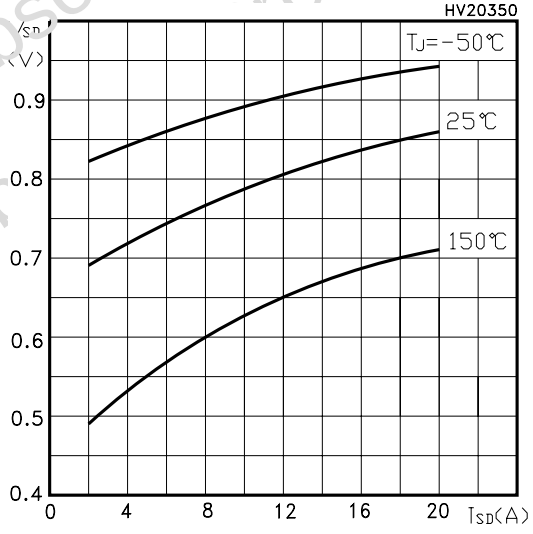

### Normalized Gate Thereshold Voltage vs Temp.



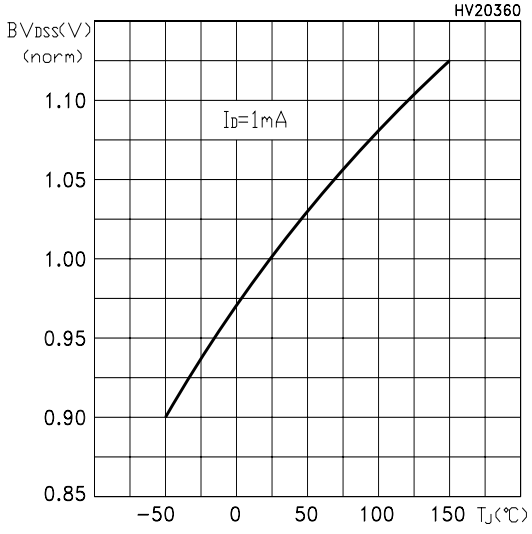

### Normalized On Resistance vs Temperature




### Source-drain Diode Forward Characteristics

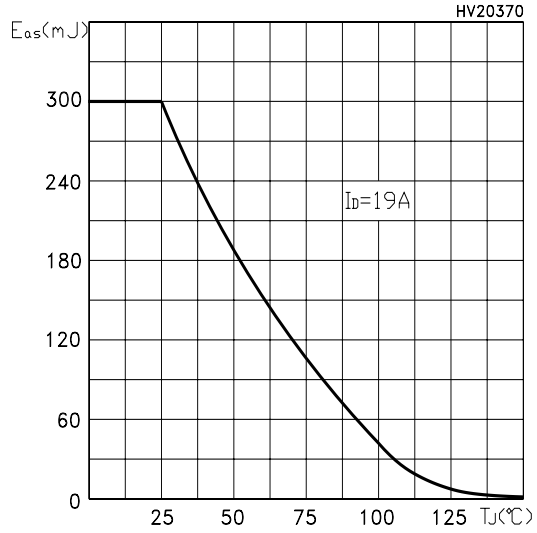



### Normalized BVDSS vs Temperature




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### Maximum Avalanche Energy vs Temperature




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Obsolete Product(s) - Obsolete Product(s)

**Fig. 1:** Unclamped Inductive Load Test Circuit

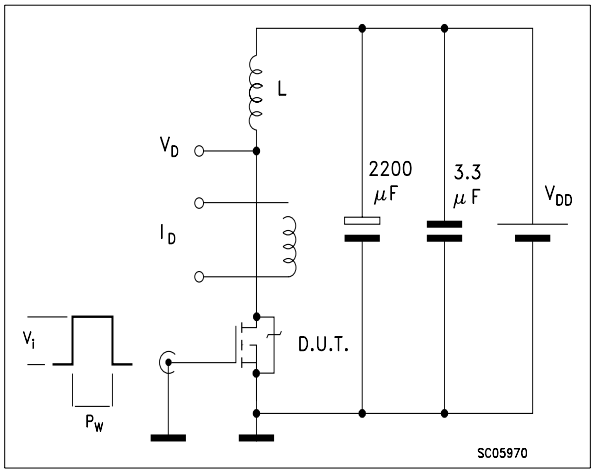



**Fig. 2:** Unclamped Inductive Waveform

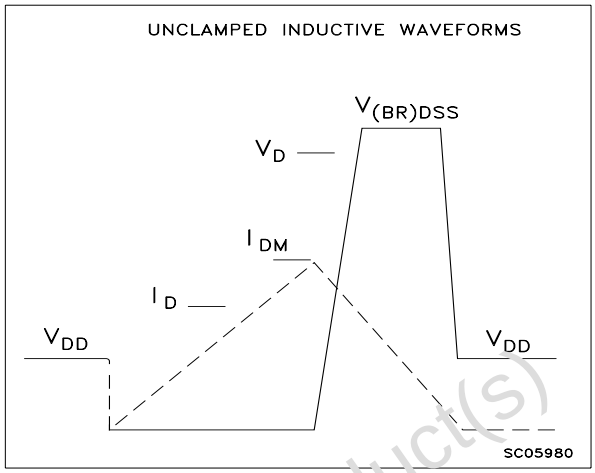



**Fig. 3:** Switching Times Test Circuit For Resistive Load

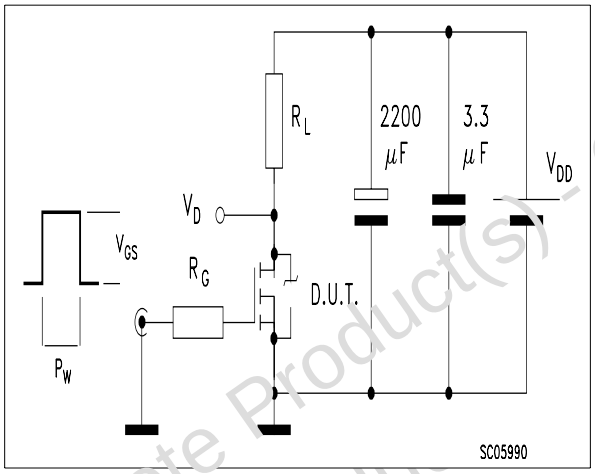



**Fig. 4:** Gate Charge test Circuit

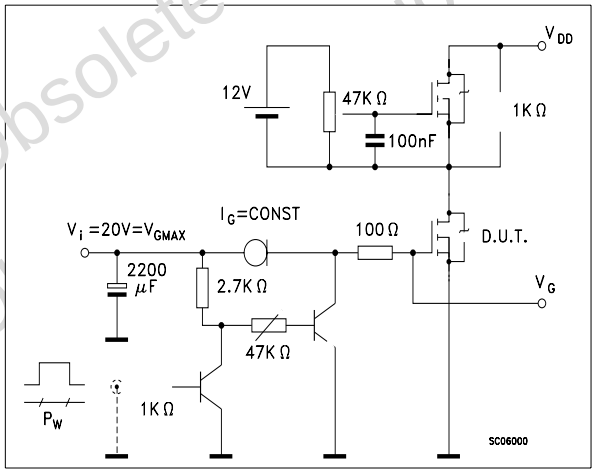
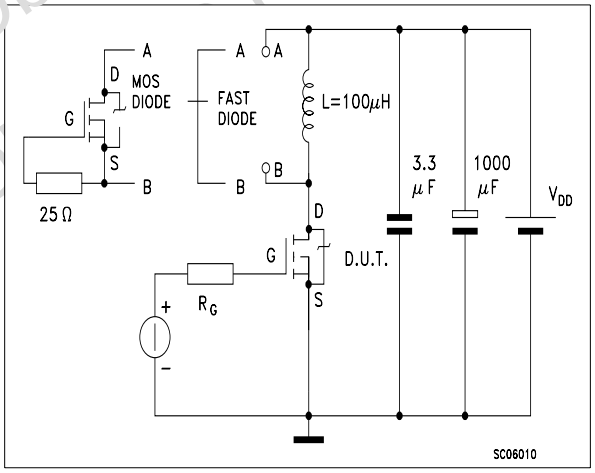


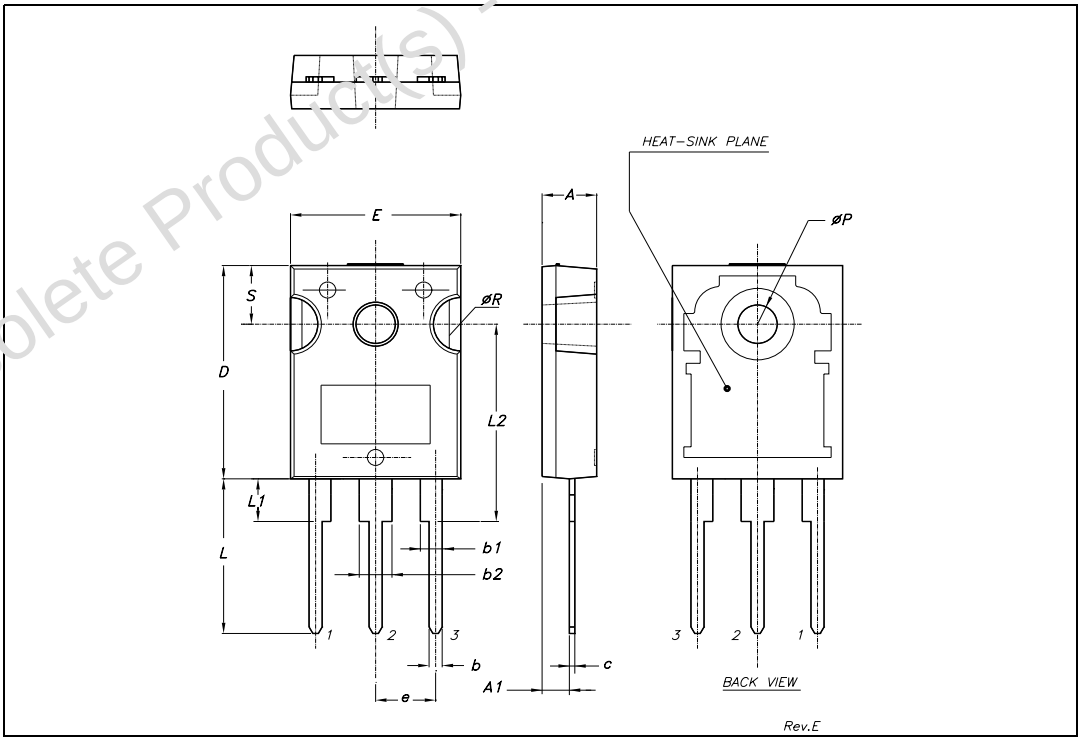

**Fig. 5:** Test Circuit For Inductive Load Switching And Diode Recovery Times




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## TO-247 MECHANICAL DATA

| DIM. | mm. | | | inch | | |
|---|---|---|---|---|---|---|
| | MIN. | TYP | MAX. | MIN. | TYP. | MAX. |
| A | 4.85 | | 5.15 | 0.19 | | 0.20 |
| A1 | 2.20 | | 2.60 | 0.086 | | 0.102 |
| b | 1.0 | | 1.40 | 0.039 | | 0.055 |
| b1 | 2.0 | | 2.40 | 0.079 | | 0.094 |
| b2 | 3.0 | | 3.40 | 0.118 | | 0.134 |
| c | 0.40 | | 0.80 | 0.015 | | 0.03 |
| D | 19.85 | | 20.15 | 0.781 | | 0.793 |
| E | 15.45 | | 15.75 | 0.608 | | 0.620 |
| e | | 5.45 | | | 0.214 | |
| L | 14.20 | | 14.80 | 0.560 | | 0.582 |
| L1 | 3.70 | | 4.30 | 0.14 | | 0.17 |
| L2 | | 18.50 | | | 0.728 | |
| øP | 3.55 | | 3.65 | 0.140 | | 0.143 |
| øR | 4.50 | | 5.50 | 0.177 | | 0.216 |
| S | | 5.50 | | | 0.216 | |




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